

MOS FIELD EFFECT TRANSISTOR μ PA1744TP

SWITCHING N-CHANNEL POWER MOS FET

DESCRIPTION

The μ PA1744TP is N-channel MOS FET device that features a low on-state resistance and excellent switching characteristics, and designed for high voltage applications such as DC/DC converter.

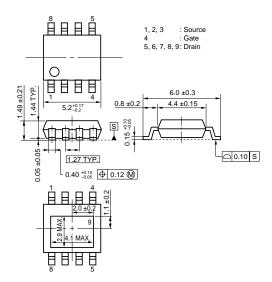
FEATURES

- Low on-state resistance $R_{DS(on)} = 30 \text{ m}\Omega \text{ MAX.}$ (Vgs = 10 V, Ip = 5.0 A)
- Low input capacitance
 C_{iss} = 3400 pF TYP. (V_{DS} = 10 V, V_{GS} = 0 V)
- Built-in gate protection diode
- Small and surface mount package (Power HSOP8)

ORDERING INFORMATION

PART NUMBER	PACKAGE
μ PA1744TP	Power HSOP8

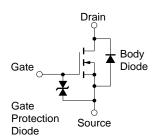
PACKAGE DRAWING (Unit: mm)



ABSOLUTE MAXIMUM RATINGS (TA = 25°C, Unless otherwise noted, all terminals are connected.)

Drain to Source Voltage (Vgs = 0 V)	VDSS	100	V
Gate to Source Voltage (Vps = 0 V)	Vgss	±20	V
Drain Current (DC) (Tc = 25°C)	ID(DC)	±10	Α
Drain Current (pulse) Note1	ID(pulse)	±30	Α
Total Power Dissipation (Tc = 25°C)	P _{T1}	39	W
Total Power Dissipation (T _A = 25°C) Note2	P _{T2}	3.0	W
Channel Temperature	T_ch	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C
Single Avalanche Current Note3	las	10	Α
Single Avalanche Energy Note3	Eas	10	mJ

EQUIVALENT CIRCUIT



- **Notes 1.** PW \leq 10 μ s, Duty Cycle \leq 1%
 - 2. Mounted on glass epoxy board of 1 inch x 1 inch x 0.8 mm
 - 3. Starting T_{ch} = 25°C, V_{DD} = 50 V, R_G = 25 Ω , V_{GS} = 20 \rightarrow 0 V, L = 100 μ H

Remark The diode connected between the gate and source of the transistor serves as a protector against ESD.

When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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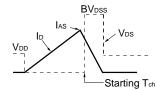
ELECTRICAL CHARACTERISTICS (TA = 25°C, Unless otherwise noted, all terminals are connected.)

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	IDSS	V _{DS} = 100 V, V _{GS} = 0 V			10	μΑ
Gate Leakage Current	Igss	Vgs = ±20 V, Vps = 0 V			±10	μΑ
Gate Cut-off Voltage	V _{GS(off)}	V _{DS} = 10 V, I _D = 1 mA	2.5	3.0	3.5	V
Forward Transfer Admittance Note	y _{fs}	V _{DS} = 10 V, I _D = 5.0 A	7	14		S
Drain to Source On-state Resistance Note	RDS(on)	Vgs = 10 V, ID = 5.0 A		23	30	mΩ
Input Capacitance	Ciss	V _{DS} = 10 V		3400		pF
Output Capacitance	Coss	V _G S = 0 V		390		pF
Reverse Transfer Capacitance	Crss	f = 1 MHz		200		pF
Turn-on Delay Time	td(on)	V _{DD} = 50 V, I _D = 5.0 A		22		ns
Rise Time	tr	V _{GS} = 10 V		10		ns
Turn-off Delay Time	td(off)	R _G = 10 Ω		55		ns
Fall Time	tf			7		ns
Total Gate Charge	Q _G	V _{DD} = 80 V		66		nC
Gate to Source Charge	Qgs	V _{GS} = 10 V		12		nC
Gate to Drain Charge	Q _{GD}	I _D = 10 A		22		nC
Body Diode Forward Voltage Note	V _{F(S-D)}	IF = 10 A, VGS = 0 V		0.8		V
Reverse Recovery Time	trr	IF = 10 A, Vgs = 0 V		65		ns
Reverse Recovery Charge	Qrr	di/dt = 100 A/μs		170		nC

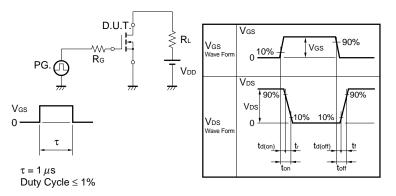
Note Pulsed: PW \leq 350 μ s, Duty Cycle \leq 2%

TEST CIRCUIT 1 AVALANCHE CAPABILITY

$V_{GS} = 20 \rightarrow 0 \text{ V}$ $PG. \bigcirc PG. \bigcirc PG.$



TEST CIRCUIT 2 SWITCHING TIME



TEST CIRCUIT 3 GATE CHARGE

$$\begin{array}{c|c} D.U.T. \\ \hline I_G = 2 \text{ mA} \\ \hline \downarrow \\ \hline \\ PG. \\ \hline \end{array} \begin{array}{c} S_{DU} \\ \hline \\ \hline \\ \hline \\ \end{array} \begin{array}{c} R_L \\ \hline \\ \hline \\ \hline \\ \end{array} \begin{array}{c} V_{DD} \\ \hline \\ \end{array}$$

Ip - Drain Current - A

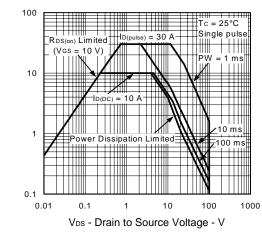
TYPICAL CHARACTERISTICS (TA = 25°C, Unless otherwise noted, all terminals are connected.)

SAFE OPERATING AREA www.DataSheet4U.Therentage of Rated Power - % Tc - Case Temperature - °C

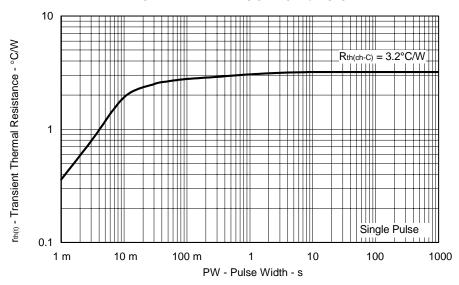
DERATING FACTOR OF FORWARD BIAS

TOTAL POWER DISSIPATION vs. CASE TEMPERATURE P_T - Total Power Dissipation - W Tc - Case Temperature - °C

FORWARD BIAS SAFE OPERATING AREA

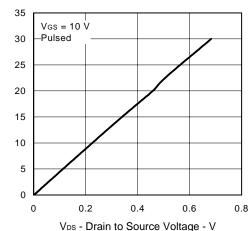


TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH

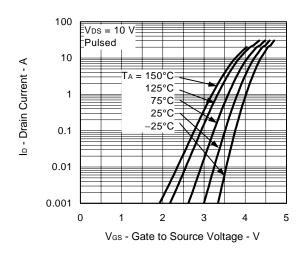


Ib - Drain Current - A

DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE

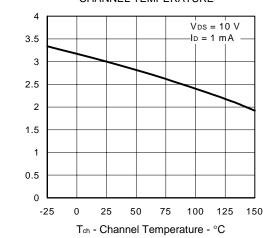


FORWARD TRANSFER CHARACTERISTICS

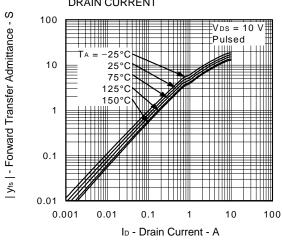


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GATE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE



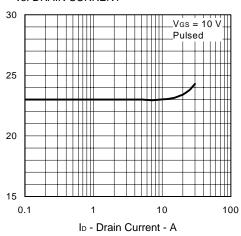
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



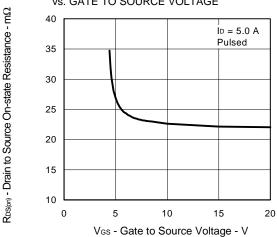
 $\mathsf{Ros}_\text{(on)}$ - Drain to Source On-state Resistance - $m\Omega$

Ves(off) - Gate Cut-off Voltage - V

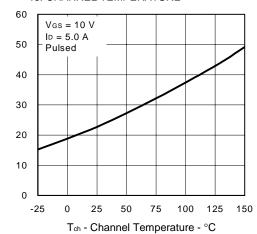
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



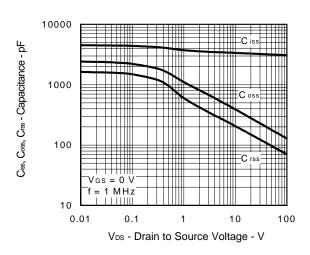
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE

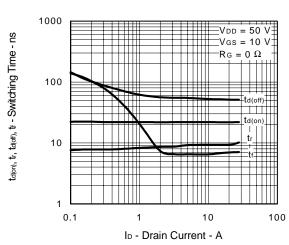


CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE

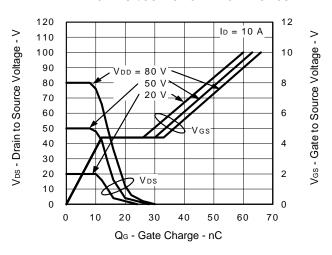


www.Data Source On-state Resistance - m

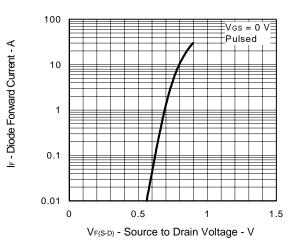
SWITCHING CHARACTERISTICS



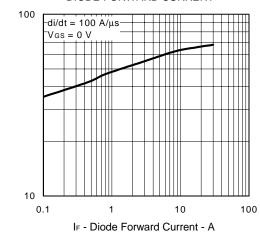
DYNAMIC INPUT/OUTPUT CHARACTERISTICS



SOURCE TO DRAIN DIODE FORWARD VOLTAGE



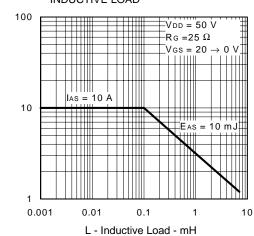
REVERSE RECOVERY TIME vs. DIODE FORWARD CURRENT



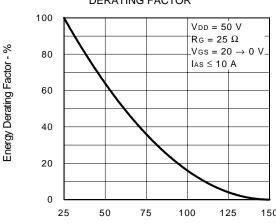
tr - Reverse Recovery Time - ns

IAS - Single Avalanche Current - A

SINGLE AVALANCHE CURRENT vs. INDUCTIVE LOAD



SINGLE AVALANCHE ENERGY DERATING FACTOR



Starting Tch - Starting Channel Temperature - °C

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